

ABSTRACT OF THE DISCLOSURE

A semiconductor device having a semiconductor substrate;
an insulating film formed on said semiconductor substrate; a
5 ferroelectric capacitor having a lower electrode, a
ferroelectric film and an upper electrode which are stacked
sequentially on the insulating film; a first hydrogen barrier
film; a first inter-layer insulating film covering said
ferroelectric capacitor; and a second inter-layer
10 insulating film stacked on the first inter-layer insulating film,
the first hydrogen barrier film being interposed between the first
and second interlayer insulating films is proposed.